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(57) **ABSTRACT**

A semiconductor device includes a substrate including a peripheral active pattern defined by a device isolation layer, a gate structure on the peripheral active pattern, and a gate spacer covering at least a portion of a side surface of the gate structure. The gate structure includes an insulating pattern structure and a metal pattern structure on the insulating pattern structure. The insulating pattern structure includes a recess having a maximum depth in a first direction parallel to a top surface of the substrate at a first height. The insulating pattern structure includes a first gate insulating pattern and a high-k dielectric layer, which are sequentially stacked on the top surface of the substrate. The gate spacer includes a protrusion inserted in the recess.

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